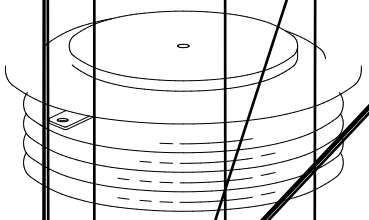
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T11C



Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KP1800/38	3800	3800	3900
KP1800/40	4000	4000	4100
KP1800/42	4200	4200	4300

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	5 mA 150 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/μs

Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		200		mA	V_D =12 V;R_L = 3 ohms;T_j = +25 °C
Gate- trigger voltage	V_{GT}	0.7	3.0		V	V_D = 12 V;R_L = 3 ohms;T_j = +25 °C
Peak negative voltage	V_{GRM}		5		V	

Delay time	t_d		3.0	2.5	μs	I_{TM}=100A; V_D=67%V_{DRM} Gate pulse:V_G=30V; R_G=10ohms; t_r=0.1μs; t_p=20μs
Turn-off time (with V_R = -5 V)	t_q			700	μs	I_{TM} =2000A; di/dt =-10A/μs; V_R =100V; dv/dt=30V/μs ; V_D=67%V_{DRM};Tj=125
Reverse recovery charge	Q_{rr}				μC	I_{TM}=2000A di/dt=-10A/μs; V_R=100V; T_j=125

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